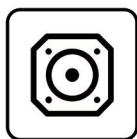


自主封測 品質把控 售後保障

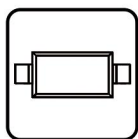
WEB | WWW.TDSEMIC.COM



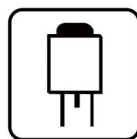
電源管理



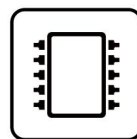
顯示驅動



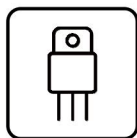
二三極管



LDO穩壓器



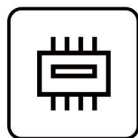
觸摸芯片



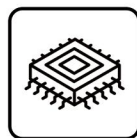
MOS管



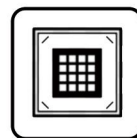
運算放大器



存儲芯片



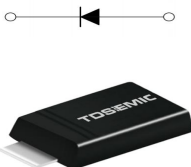
MCU



串口通信

BAT46W-TD

產品規格說明書

SCHOTTKY BARRIER DIODE			
SOD-123  Marking : S9		Features High breakdown voltage Low turn-on voltage Guard ring construction for transient protection	

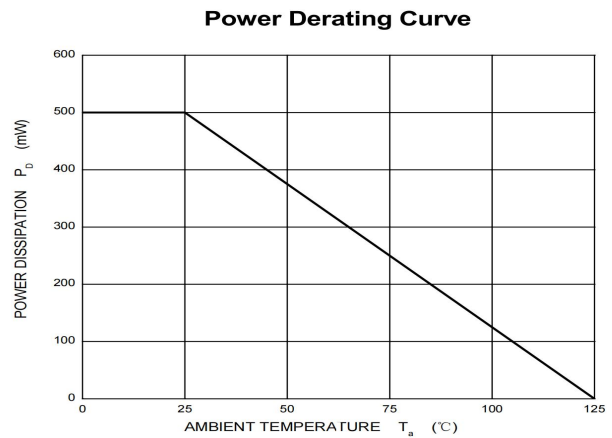
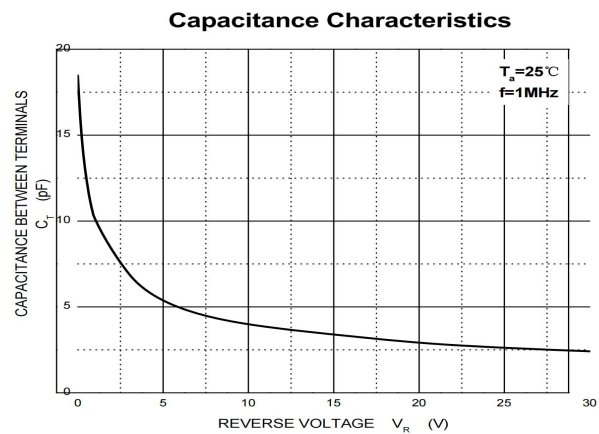
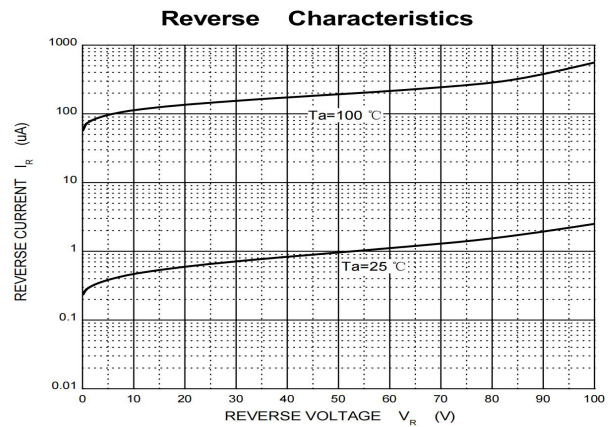
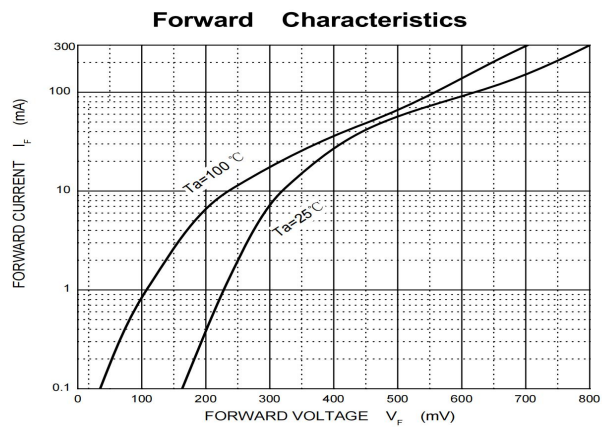
Maximum Ratings @Ta=25°C			
Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	VRRM	100	V
Working peak reverse voltage	VRWM		
Forward continuous current	IF	150	mA
Repetitive peak forward current (Note 1) @ tp < 1.0s, Duty Cycle < 50%	IFRM	350	mA
Non-repetitive Peak Forward surge current @ t = 8.3ms	IFSM	750	mA
Power dissipation	PD	500	mW
Thermal resistance junction to ambient air	RθJA	200	°C/W
Junction temperature	Tj	125	°C
Storage temperature	TSTG	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage(Note 2)	VR	IR= 100μA	100			V
Reverse voltage leakage current	IR	VR1= 1.5V			0.3	μA
		VR2= 10V			0.5	
		VR3= 50V			1	
		VR4= 75V			2	
Forward voltage(Note 2)	VF	IF1= 0.1mA			0.25	V
		IF2= 10mA			0.45	
		IF3= 250mA			1	
Diode capacitance	CT	VR=0, f=1MHz		20		pF
		VR=1V, f=1MHz		12		

Notes: 1. Part mounted on FR-4 board with recommended pad layout.

2. Short duration pulse test used to minimize self-heating effect.

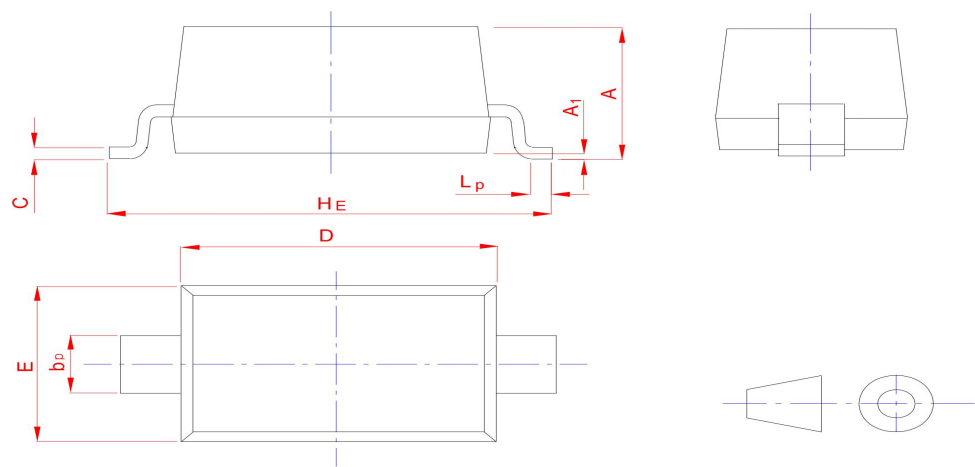
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20